

Title (en)
METHOD FOR MANUFACTURING A MASK HAVING SUBMILLIMETRIC APERTURES FOR A SUBMILLIMETRIC ELECTRICALLY CONDUCTIVE GRID, MASK HAVING SUBMILLIMETRIC APERTURES, AND SUBMILLIMETRIC ELECTRICALLY CONDUCTIVE GRID

Title (de)
VERFAHREN ZUR HERSTELLUNG EINER MASKE MIT SUBMILLIMETRISCHEN ÖFFNUNGEN FÜR EIN SUBMILLIMETRISCHES ELEKTRISCH LEITFÄHIGES GITTER, MASKE MIT SUBMILLIMETRISCHEN ÖFFNUNGEN UND SUBMILLIMETRISCHES ELEKTRISCH LEITFÄHIGES GITTER

Title (fr)
PROCEDE DE FABRICATION D'UN MASQUE A OUVERTURES SUBMILLIMETRIQUES POUR GRILLE ELECTROCONDUCTRICE SUBMILLIMETRIQUE, MASQUE A OUVERTURES SUBMILLIMETRIQUES, GRILLE ELECTROCONDUCTRICE SUBMILLIMETRIQUE

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Abstract (en)
[origin: WO2010034944A1] The invention relates to a method for manufacturing a mask (1) having submillimetric apertures (10), wherein: - a solution of stabilized colloidal nanoparticles dispersed in a solvent is deposited for a mask layer, the particles having a given vitreous transition temperature Tg; - the mask layer is dried at a temperature lower than said temperature Tg until a mask having a two-dimensional array of submillimetric apertures is obtained with substantially straight mask area edges in a so-called array mask area; - a free mask area is formed on said surface through the mechanical and/or optical shrinkage of at least one peripheral portion of the array mask area. The invention also relates to said array mask (1) and to the grid with an electrically conductive solid area thus obtained.

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